In The Claims:

1. (original) A non-volatile memory, comprising:

a substrate;

a word-line on the substrate;

a charge trapping layer between the substrate and the word-line;

a contact disposed over the substrate electrically connecting with the word-lind; and

a protective metal line electrically connecting with the contact and with a grounding doped region in the substrate, wherein the protective metal line has a first resistance higher than a second resistance of the word-line.

2. (original) The non-volatile memory of claim 1, wherein the protective metal line has a first width smaller than a second width of the word-line.

3. (original) The non-volatile memory of claim 1, wherein the protective metal line has a first thickness smaller than a second thickness of the word-line.

4. (original) The non-volatile memory of claim 1, wherein the protective metal line is electrically connected with the grounding doped region via another contact.

5. (original) The non-volatile memory of claim 1, wherein the charge trapping layer comprises a silicon oxide/silicon nitride/silicon oxide (ONO) composite layer.

6. (original) The non-volatile memory of claim 1, wherein the word-line comprises:

a polysilicon line on the charge trapping layer; and

a metal silicide line on the polysilicon line.

7. (original) The non-volatile memory of claim 6, wherein the metal silicide line comprises tungsten silicide (Wsi_x).

Claims 8-14 (canceled)